

PAUL SCHERRER INSTITUT



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Analog Signal Processing for Particle Detectors

PSI, LTP-Seminar, 12.06.2017

Citation of a slightly dispirited assistant I met during the early days of my studies:

“If you need an amplifier then try to build an oscillator, I am sure it will never oscillate, but if you need an oscillator then try to build an amplifier...”

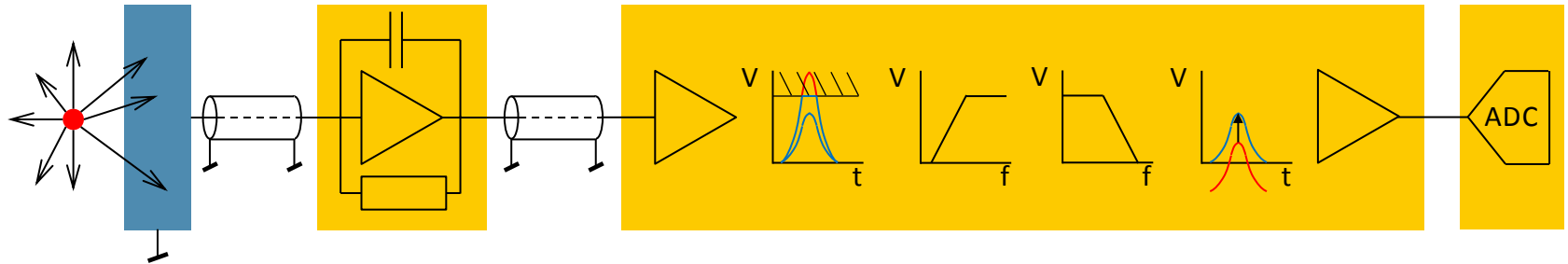
Of course this statement is not true, but there are a couple of reasons why an oscillator may not oscillate whereas an amplifier does.



Topics

- analog signal processing
- charge and current preamplifier
- pulse shaping
- examples

Analog Signal Processing for Particle Detectors

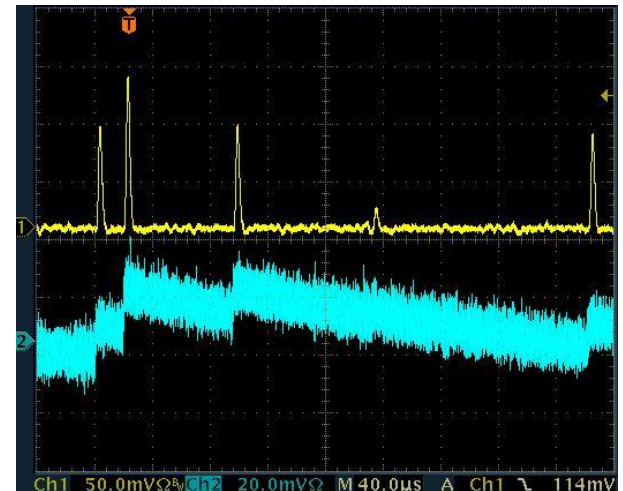


Mostly linear treatment of weak currents caused by small charges deposited or generated within a detector

Its goal is the extraction of information out of the weak generally noisy signals with the best possible S/N-ratio and/or the lowest possible timing jitter

It includes at least three steps:

- signal capturing and (pre-)amplification
- pulse shaping by bandwidth manipulations
- signal conditioning for the following stage



Ch1(yellow): signal after pulse shaping

Ch2(blue): signal e.g. after a charge sensitive preamplifier

Keywords in Analog Signal Processing are:

- Gain
- Bandwidth
- Dynamic input/output range
- Stability
- Linearity
- Pulse shaping/Filtering
- Noise
- Distortion
- Drive strength
- Powering and grounding scheme
- Power consumption and cooling
- Mechanical considerations (housing, size, integration)

Not covered in the above list are topics specific for **non-linear analog processing** (e.g. frequency mixing as it is usual done in RF-communication, ...)

What has to be known to be able to develop a signal processing chain

from the experiment:

- parameters to be measured (energy, position, intensity, time of arrival, counts, ...)
- expected hit rate and their time distribution (poisson, bunch,...)
- other particles giving signals which has to be suppressed (e.g. by energy evaluation)
- environment conditions(magnetic fields, vacuum,)

from the detector:

- amount of charge deposited
- charge collection time
- detector recovery time
- detector capacitance and resistivity
- part of signal containing information
- readout scheme (e.g. charge division, time delay, ...)
- number of channels
- operating voltage

What has to be known to develop a signal processing chain

- **from the next DAQ stage:**
- type of stage (discriminator, counter, TDC, ADC, ...)
- input type (single ended, differential)
- input voltage or current range
- bias point
- input impedance
- input bandwidth or sampling frequency (for analog signals)
- minimum pulse width (for digital signals)

Applicable for Measurements of Energy deposited on detector

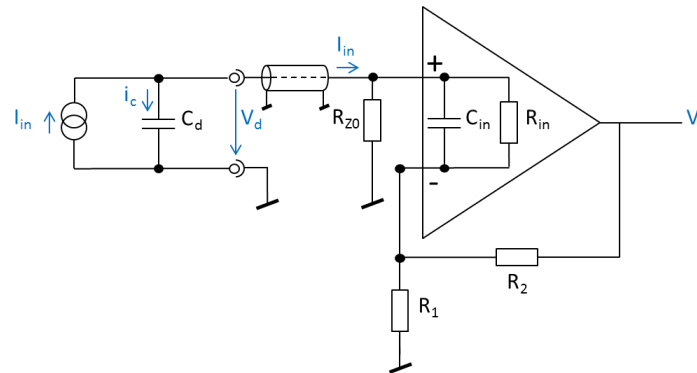
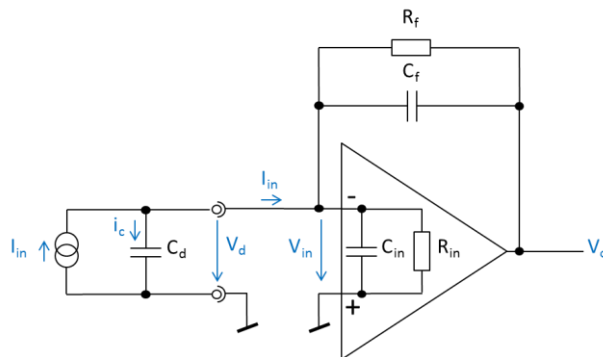
$$E_{particle} \propto Q_s = \int^{\tau} i_s(t) dt \quad \text{with } \tau \gg T_{\text{charge_collection}}$$

typical dynamic range: $\frac{Q_{s,max}}{Q_{s,min}} = 10^3 \dots 10^5$ (= 60 ... 100 dB or = 10...17 bits)

Energy information is a charge => Integration of current is needed

Charge sensitive preamplifier:

The most common ways are either to use a charge sensitive preamplifier based on a operational amplifier or especially when there is a cable in between detector and preamplifier a resistor with the cable impedance followed by a voltage amplifier:



Charge Sensitive amplifier using an operational amplifier:

Operational Amplifier:

Open loop gain $dV_{out}/dV_{in} = -A$ ($|A| \approx 1E3-1E4 \gg 1$)

Input resistance $R_{in} \approx 10 - 100 \text{ M}\Omega$ (or even higher)

Negative feedback forces $V_{in} \approx 0$ (but not = 0)

=> partial charge transfers from C_d to C_f

Reason for the only partial transfer:

Amplifier transforms the feedback capacitor C_f into a dynamic input capacitance

$$C_{in} = \frac{Q_{in}}{V_{in}} = \frac{C_f \cdot V_f}{V_{in}} = \frac{C_f \cdot V_{in} \cdot (A+1)}{V_{in}} = C_f (A + 1)$$

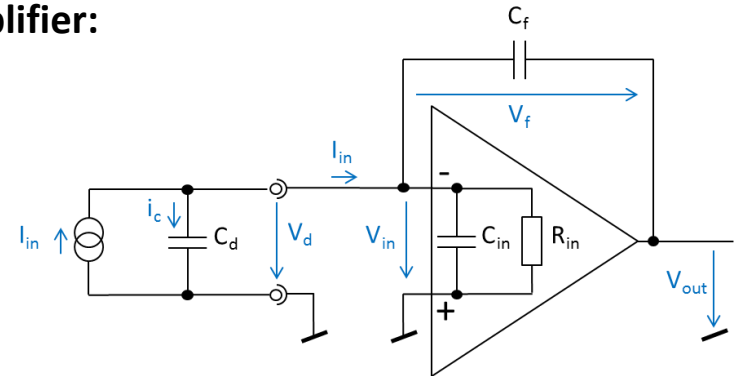
=> Free charges from the detector are divided on both capacitances (C_d and C_{in}) with the

ratio: $v_{in} = Q_d/C_d = Q_{in}/C_{in} \Rightarrow Q_d = Q_{in} \cdot C_d/C_{in}$ and $Q_{tot} = Q_d + Q_{in} = Q_{in} (C_d/C_{in} + 1)$

$$\Rightarrow \frac{Q_{in}}{Q_{tot}} = \frac{1}{\left(\frac{C_d}{C_{in}} + 1\right)}$$

Charge sensitivity of the amplifier: $A_{VQ} = \frac{V_o}{Q_{in}} = \frac{-A}{A+1} \cdot \frac{1}{C_f} \approx -\frac{1}{C_f} \left[\frac{V}{C} \right]$

Attention: this circuit will not really work, see next slide

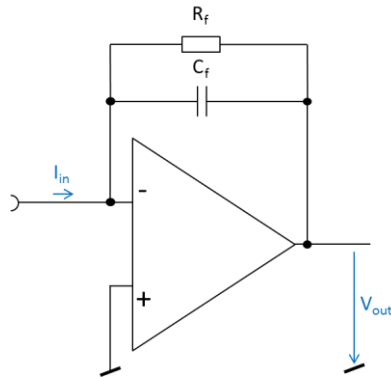
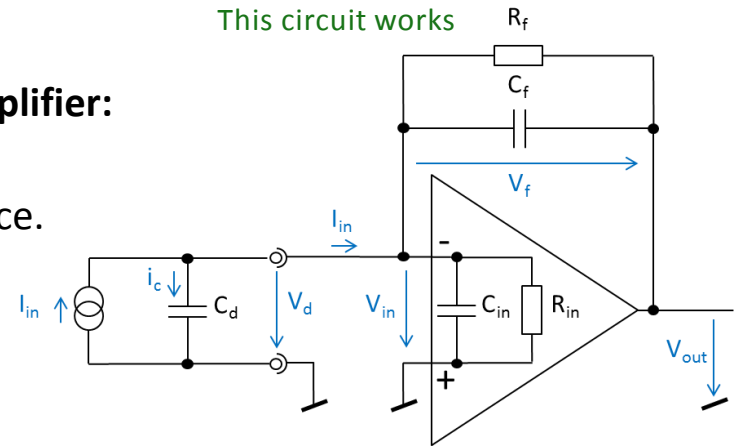


Preamplifier for Charge Measurements

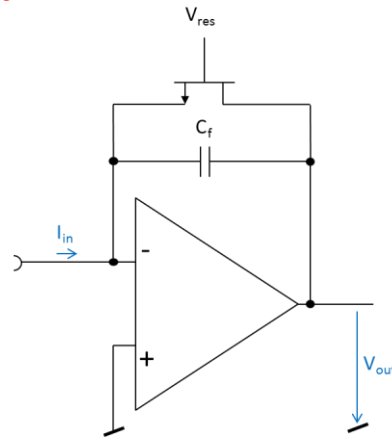
Charge Sensitive amplifier using an operational amplifier:

The previously shown circuit will not work, as there is no significant discharge of the feedback capacitance. The amplifier would integrate up until it saturates.

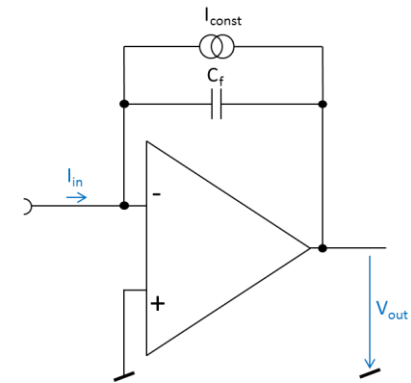
=> discharge mechanism needed:



$\tau = R_f \cdot C_f >$ charge collection time
 larger τ : - increases linearity but
 - reduces gain
 has an exponential slope ($dU \sim e^{-t/\tau}$)



reset by a transistor (normally not after each event)
 voltage V_{res} may be generated by a comparator with hysteresis switching the transistor on after V_{out} reaches a certain level
 generates unpredictable dead-times



$I_{const} \ll I_{in}$
 reduces gain
 has a linear slope ($dU/dt = I_{const}/C_f$)
 may be harder affected by temperature variations than resistor

Dynamic Range of Amplifiers

Dynamic Range of Amplifiers:

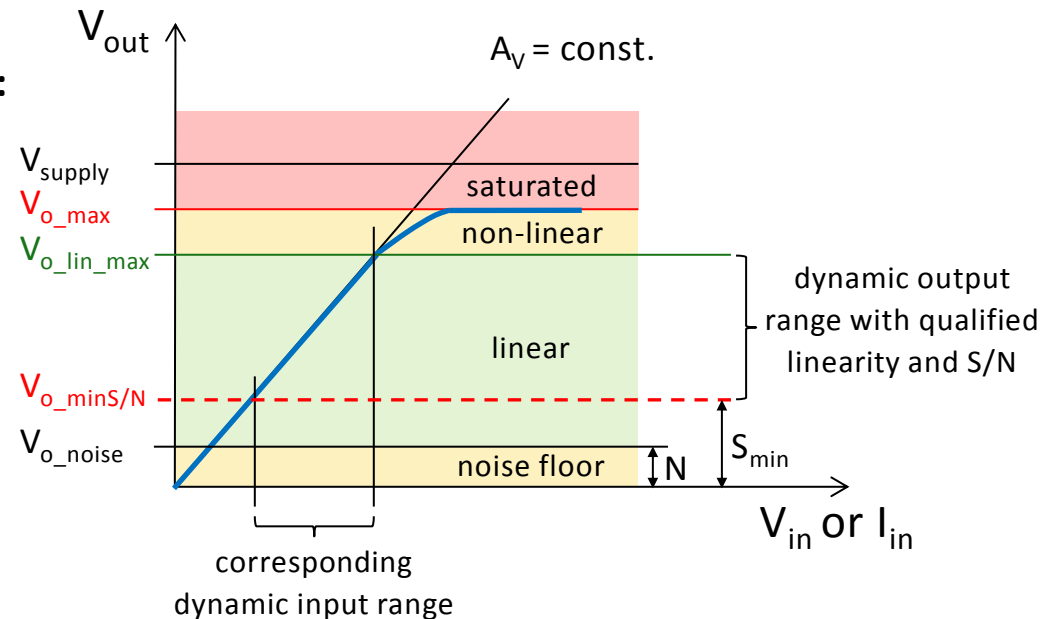
Ratio between largest (S_{max}) and smallest (S_{min}) signal for which the amplifier works within its specifications

It is typically expressed in [dB]: $DR = 20 \cdot \log_{10} \left(\frac{S_{max}}{S_{min}} \right)$ [dB]

Rem: The dynamic range can be expressed for output or input signals. In a perfect linear system it would be the same.

For precision measurement systems:

The specification of a minimum S/N-ratio and enhanced linearity requirements reduce the available dynamic range of the system.



Preamplifier for Current Measurements

Applicable for event counting at high counting rates

Remark: Current preamplifier (also called transimpedance amplifier) are not faster but they have almost no tail what makes their signals shorter

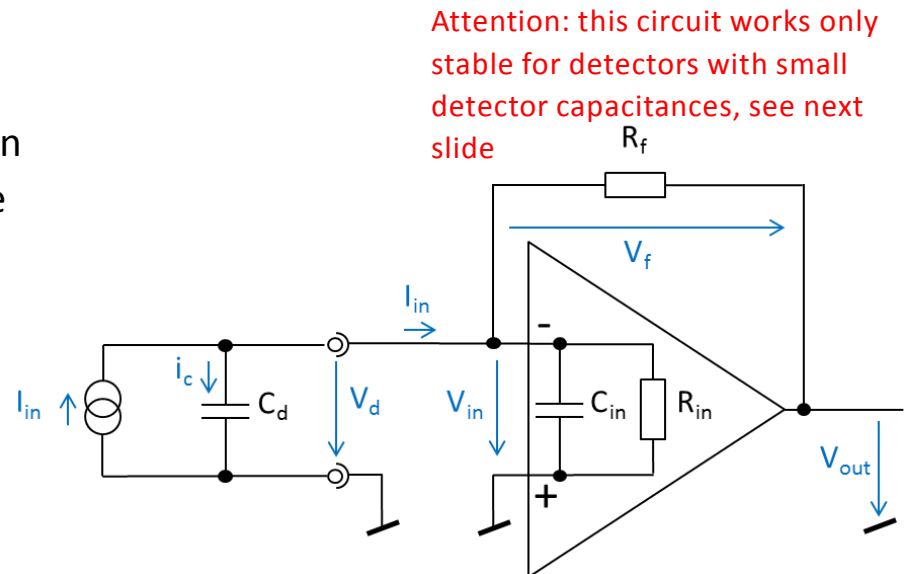
Characteristics:

- Best for high counting rates
- poorer noise performance compared to charge sensitive preamplifiers
- more affected by stability issues especially for detectors with high detector capacitance

Transimpedance preamplifier (TIA):

the working principle is quite similar than for the charge amplifier except that the feedback resistor can not store charges

=> the main topic here is stability



Preamplifier for Current Measurements

Stability is affected by detector capacitance

Amplifier OPA657 f_{GBW} 1,6E+9 Hz

DC Performance: Open Loop Voltage Gain:

OL Gain [dB]	Frequency [Hz]
70	1,0E+0
70	350,0E+3
0	1,6E+9

AC Performance: Small Signal Voltage Gain

Gain [V/V]	Gain dB	Bandwidth [Hz]
7	16,90	350,0E+6
10	20,00	275,0E+6
20	26,02	90,0E+6
20	26,02	90,0E+6

Input Common Mode Capacitance
C_CM 4,5E-12 F

Detector Capacitance
Capacitance C_J 10,0E-12 F

Amplifier

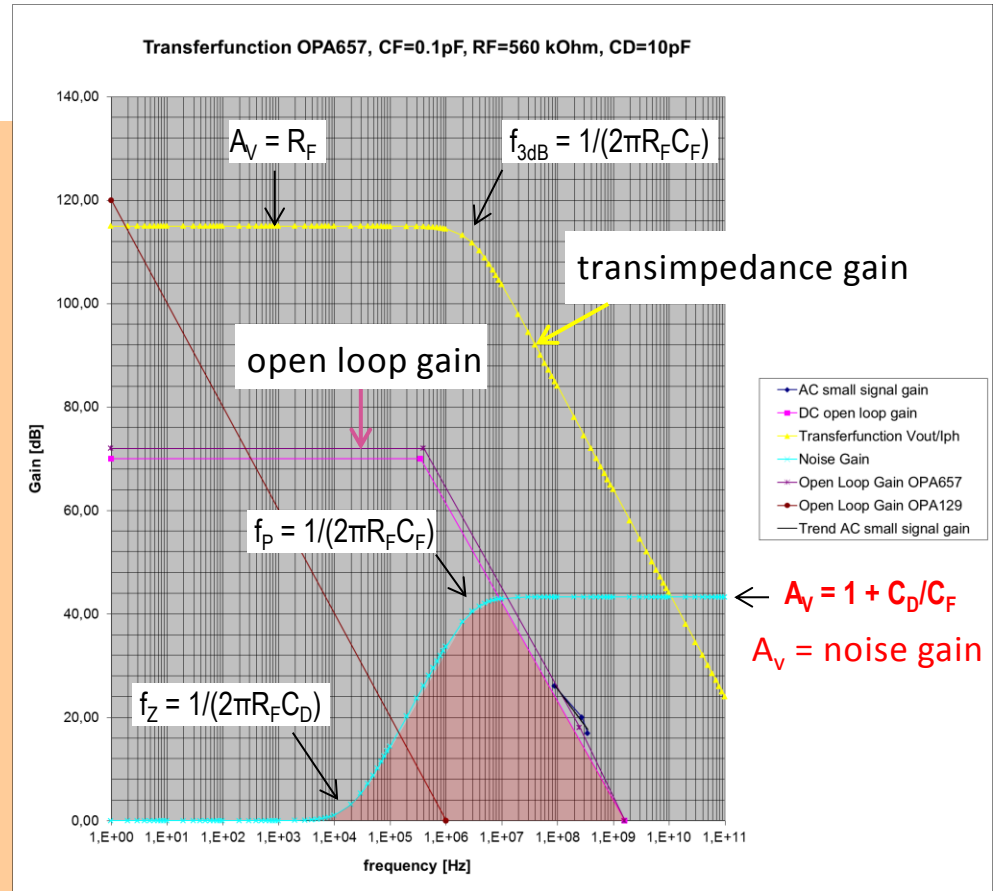
choose RF 560,0E+3 Ohm

calculated CF min. 42,7E-15 F

added safety 57,3E-15 F

calculated: CF 100,0E-15 F Annahme: C_CM + C_J >> CF

calculated 3dB point of TF 2,84E+06 Hz



detector capacitance adds noise gain and bandwidth not available to the signal

optimum gain-bandwidth and noise performance when f_p close to open loop gain curve

becomes unstable when f_p outside the open loop gain curve

Reasons for pulse shaping:

- **Shaping towards increased pulse width:**

=> **Bandwidth-reduction**

- Improve of Signal-to-Noise Ratio
- Pulse conditioning to match next stage requirements (e.g. stretching & rounding of sharp peaks for amplitude measurement with an ADC at a given f_{sampling})

- **Shaping towards reduced pulse width**

=> **Improve of Pulse Pair Resolution (pile-up reduction):**

- Increase of maximum count-rate
- Minimization of energy-measuring errors
- Dead-time or dead time variation reduction

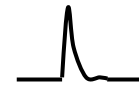
- **Other, sometimes included objectives:**

- Reduction of baseline problems
- Minimization of timing errors

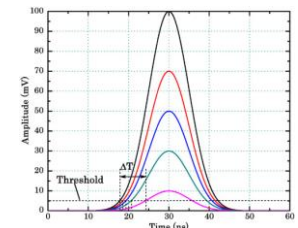
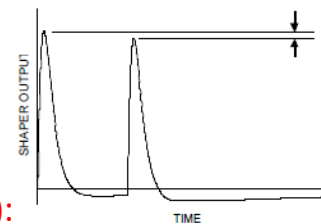
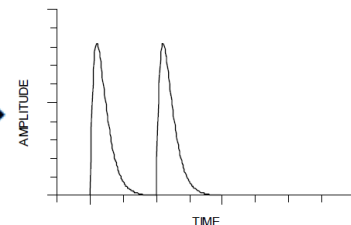
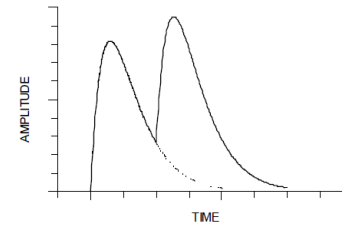
Conflicting objectives (e.g. best S/N-Ratio at max. count-rate):

=> "Optimum shaping" is usually an application dependent compromise and has to be specified!

Detector Pulse



Shaper Output

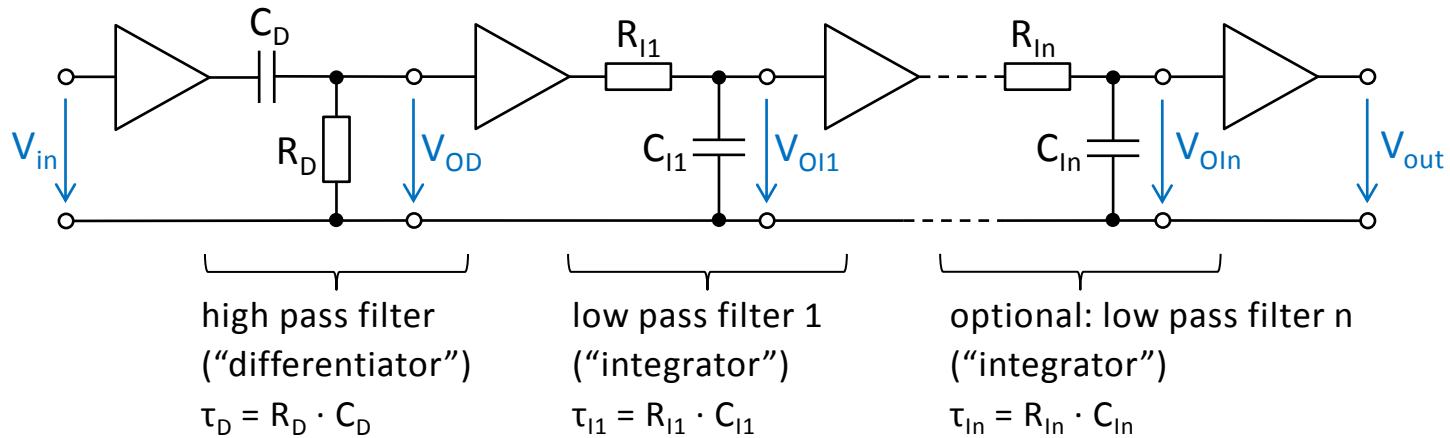


Most common pulse shaping methods:

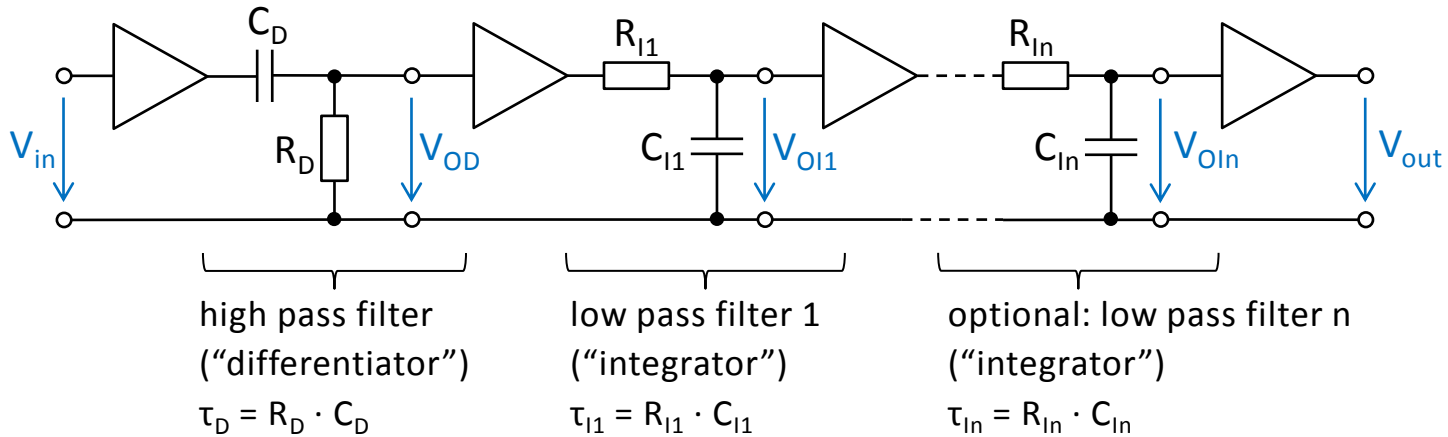
1. CR-RC Pulse Shaping
2. Pole-Zero Cancellation
3. Delay-Line Pulse Shaping
4. Gaussian Filter
5. Raised-cosine Filter
6. Sinc Filter
7. Constant Fraction Discriminator
8. Baseline Restorer

Blue = subjects in tis talk

1. CR-(RC)ⁿ Pulse Shaping:

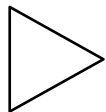


1. CR-(RC)ⁿ Pulse Shaping:

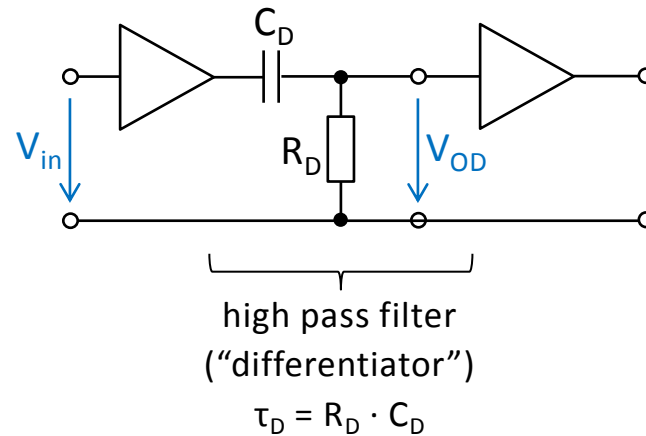


may have as well further
"differentiators" in between

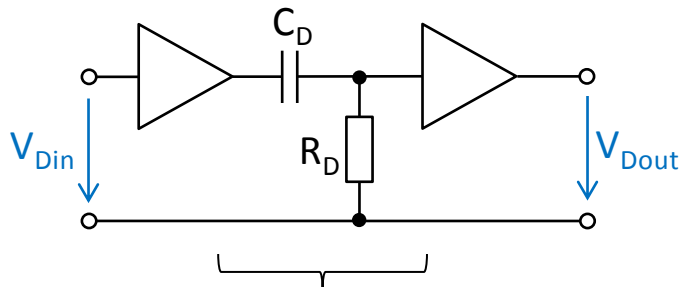
Symbol:



= voltage amplifier with high
input impedance



CR - Pulse Shaping (“differentiator”):



high pass filter (“differentiator”)

$$\tau_D = R_D \cdot C_D$$

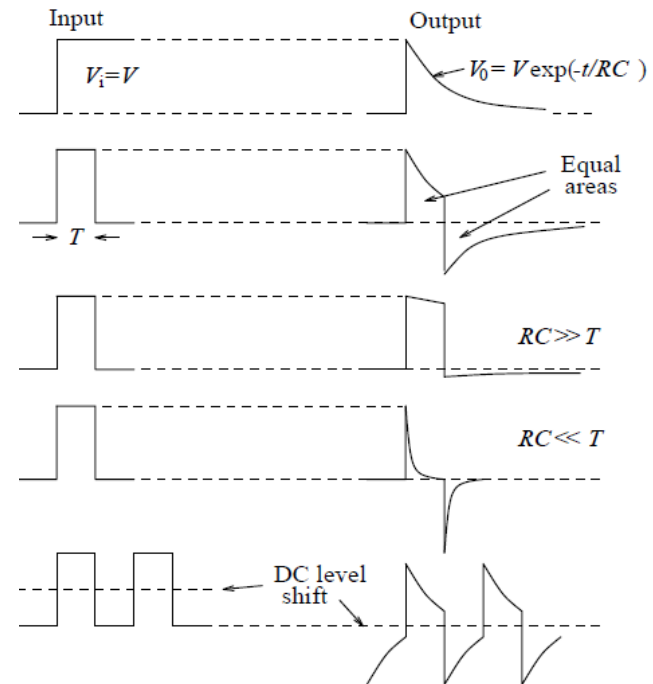
step response:

$$h(t) = \frac{V_{Dout}(t)}{V_{step}(t)} = e^{-\frac{t}{R_D C_D}}$$

Design limits for R_D :

- a lower limit for R_D is given by the max. output drive current of the previous amplifier stage and their maximum peak to peak output voltage
- to be dominant, R_D should be big compared to the output impedance of the previous amplifier

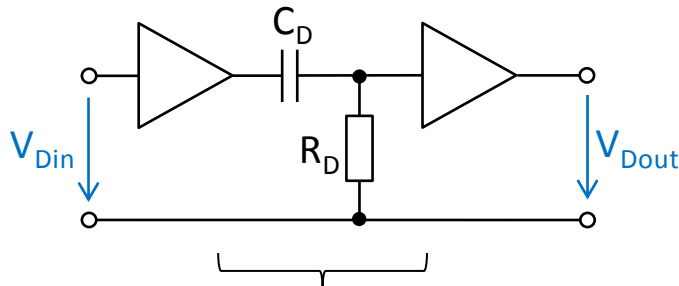
Time domain characteristics



reduces pulse width if $RC \ll T$, but has inconveniences:

- Generates bipolar output pulses (positive on rising edges and negative on falling edges) => **only applicable if falling edge has a much longer time constant**
- Peak at maximum amplitude is very short in time (bad e.g. for ADC-sampling)

CR - Pulse Shaping (“differentiator”):



high pass filter (“differentiator”)

$$\tau_D = R_D \cdot C_D$$

step response:

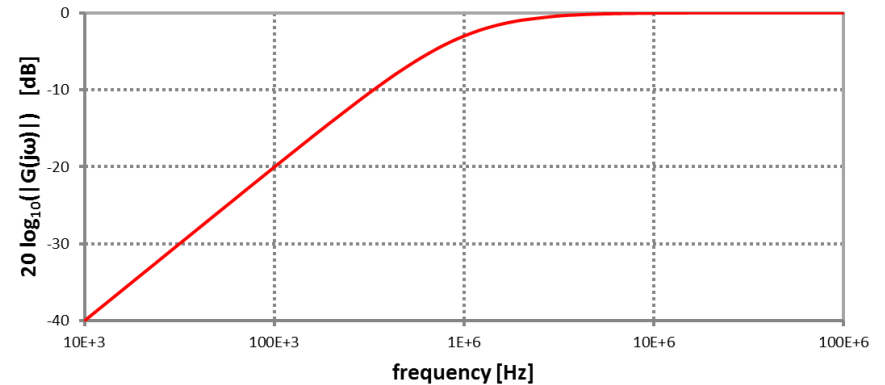
$$h(t) = \frac{V_{Dout}(t)}{V_{step}(t)} = e^{-\frac{t}{R_D C_D}}$$

transfer function:

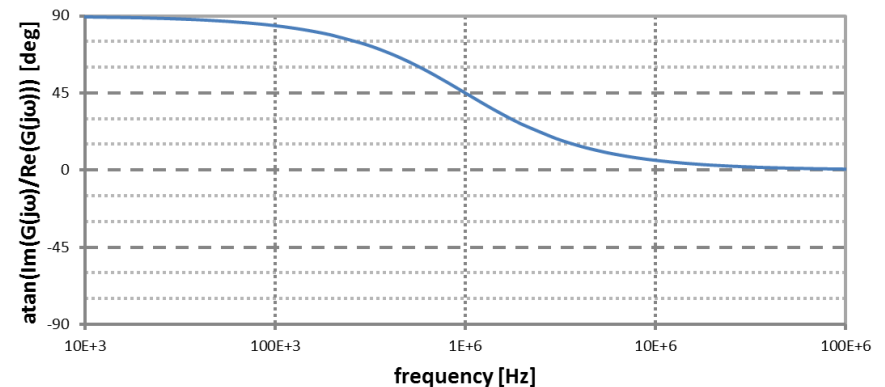
$$G_D(s) = \frac{V_{Dout}(s)}{V_{Din}(s)} = \frac{s C_D R_D}{1 + s C_D R_D}$$

Frequency domain characteristics

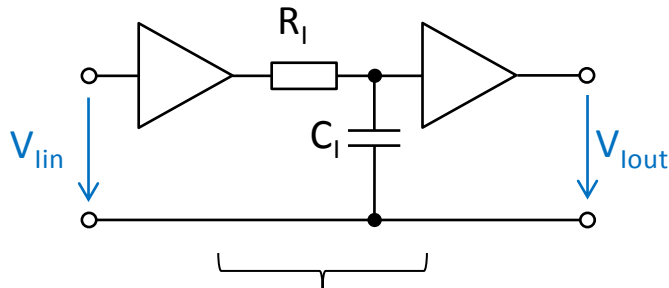
Magnitude of CR high pass with $f_{3dB} = 1/(2\pi RC) = 1E+6$ [Hz]



Phase of CR high pass with $f_{3dB} = 1/(2\pi RC) = 1E+6$ [Hz]



RC - Pulse Shaping (“integrator”):



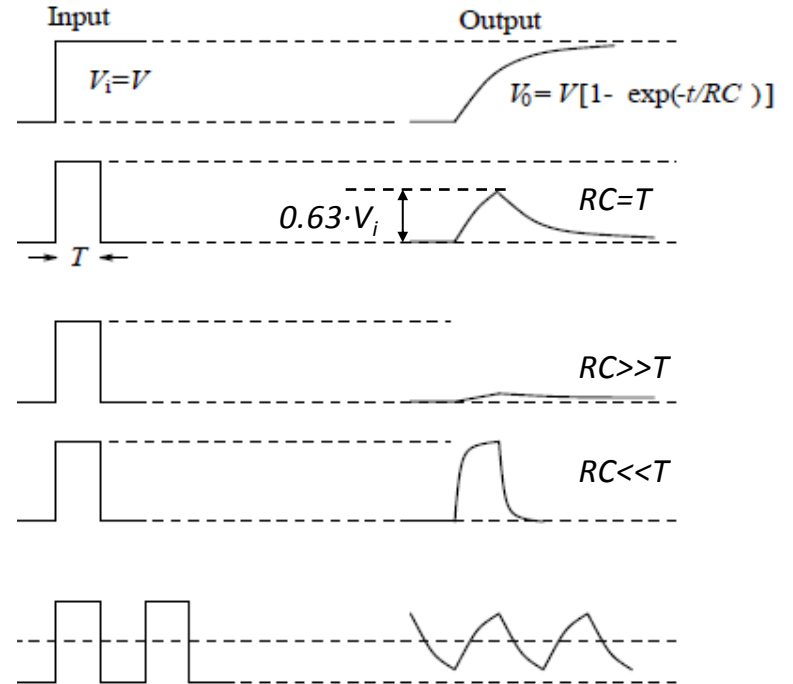
low pass filter (“integrator”)

$$\tau_1 = R_1 \cdot C_1$$

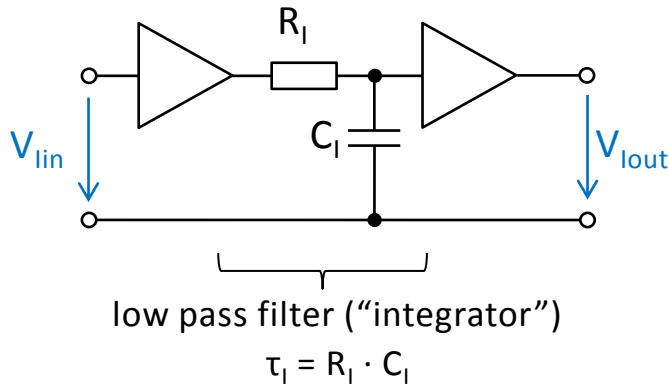
step response:

$$h(t) = \frac{V_{Iout}(t)}{V_{step}(t)} = (1 - e^{-\frac{t}{R_1 C_1}})$$

Time domain characteristics



RC - Pulse Shaping (“integrator”):



step response:

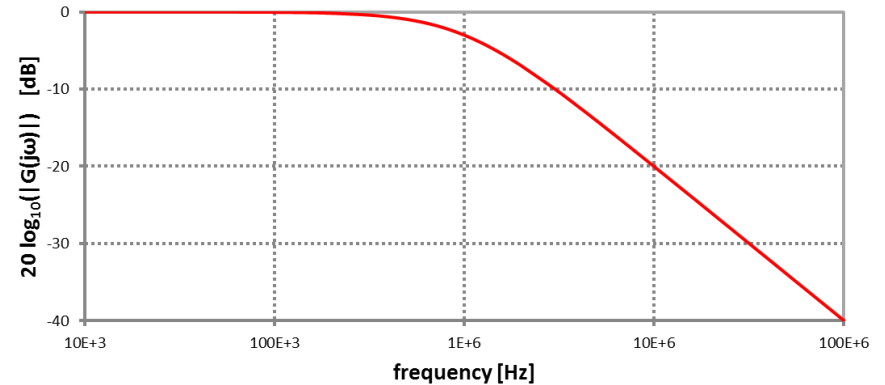
$$h(t) = \frac{V_{Iout}(t)}{V_{step}(t)} = (1 - e^{-\frac{t}{R_I C_I}})$$

transfer function:

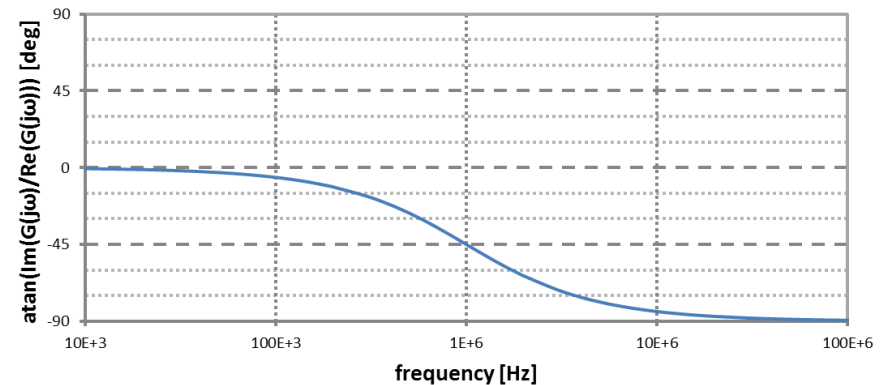
$$G_I(s) = \frac{V_{Iout}(s)}{V_{In}(s)} = \frac{1}{1 + sC_I R_I}$$

Frequency domain characteristics

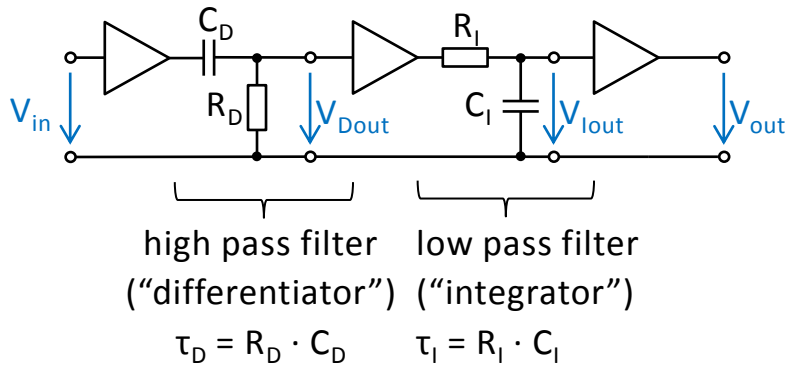
Magnitude of RC low pass with $f_{3dB} = 1/(2\pi RC) = 1E+6$ [Hz]



Phase of RC low pass with $f_{3dB} = 1/(2\pi RC) = 1E+6$ [Hz]



CR-RC Pulse Shaping (combination of a “differentiator” and an “integrator”):



a good starting point is to set $\tau_D = \tau_I$

transfer function:

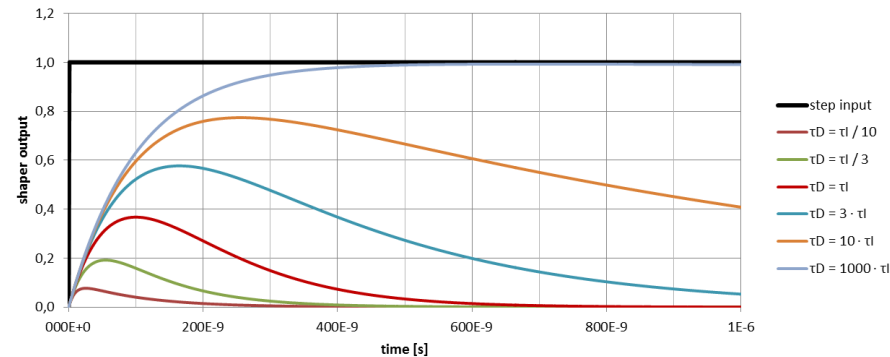
$$G_{DI}(s) = \frac{V_{out}(s)}{V_{in}(s)} = G_D(s) \cdot G_I(s) = \frac{sC_D R_D}{(1 + sC_D R_D) \cdot (1 + sC_I R_I)}$$

step response:

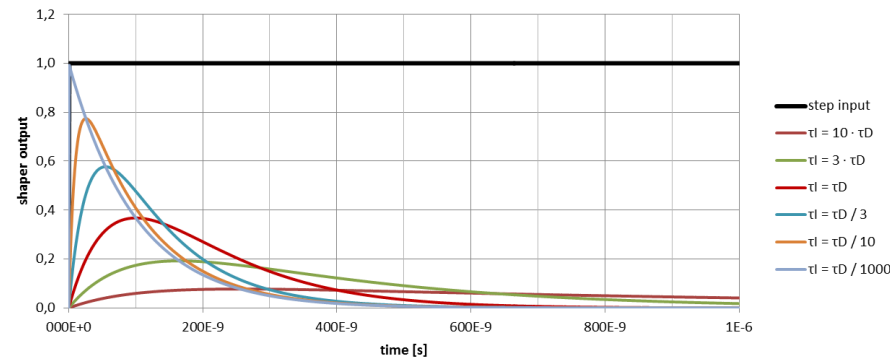
$$h(t) = \frac{v_{out}(t)}{v_{step}(t)} = \mathcal{L}^{-1} \left\{ \frac{G_{DI}(s)}{s} \right\} = \frac{\tau_D}{\tau_D - \tau_I} \cdot (e^{-\frac{t}{\tau_D}} - e^{-\frac{t}{\tau_I}})$$

and for the most common case with $\tau_D = \tau_I = \tau$: $h(t) = \frac{t}{\tau} \cdot e^{-\frac{t}{\tau}}$

step response of CR-RC shaper with $\tau_I = 100\text{ns}$ for different τ_D



step response of CR-RC shaper with $\tau_D = 100\text{ns}$ for different τ_I



CR-RC Pulse Shaping-mathematical intermezzo: Derivation of $h(t)$ for the case where $\tau_D = \tau_I$:

Starting point is the previous general formula for the CR-RC step response:

$$h(t) = \mathcal{L}^{-1} \left\{ \frac{G_{DI}(s)}{s} \right\} = \frac{v_{out}(t)}{v_{step}(t)} = \frac{\tau_D}{\tau_D - \tau_I} \cdot (e^{-\frac{t}{\tau_D}} - e^{-\frac{t}{\tau_I}})$$

As the above formula for $\tau_D = \tau_I$ apparently results in a zero divided by zero division, a limes calculation with $\Delta\tau = \tau_D - \tau_I \rightarrow 0$ may help:

$$h(t) = \lim_{\Delta\tau \rightarrow 0} \left(\frac{\tau_D}{\tau_D - \tau_I} \cdot e^{-\frac{t}{\tau_D}} \cdot (1 - e^{-t(\frac{1}{\tau_I} - \frac{1}{\tau_D})}) \right) \quad \text{factored out } e^{-\frac{t}{\tau_D}}$$

$$= \tau_D \cdot e^{-\frac{t}{\tau_D}} \cdot \lim_{\Delta\tau \rightarrow 0} \left(\frac{1 - e^{-t(\frac{\tau_D - \tau_I}{\tau_I \tau_D})}}{\tau_D - \tau_I} \right)$$

some minor cosmetics

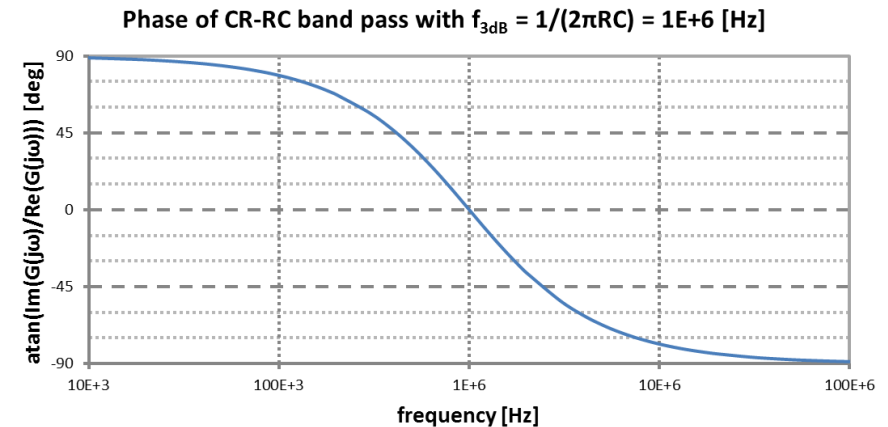
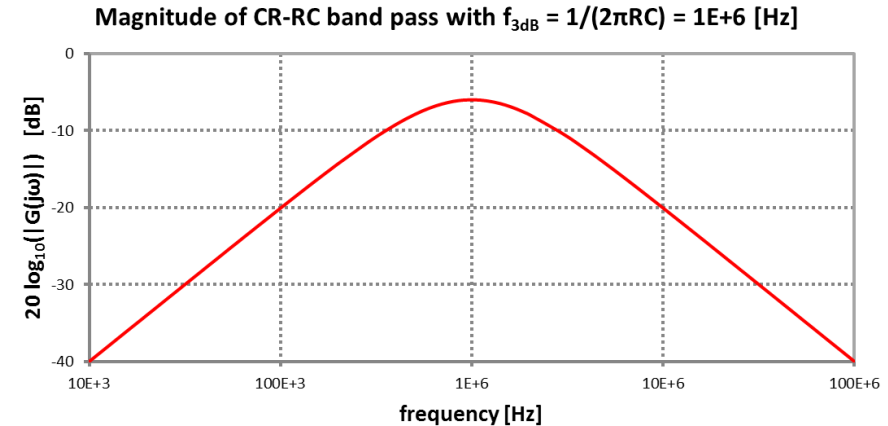
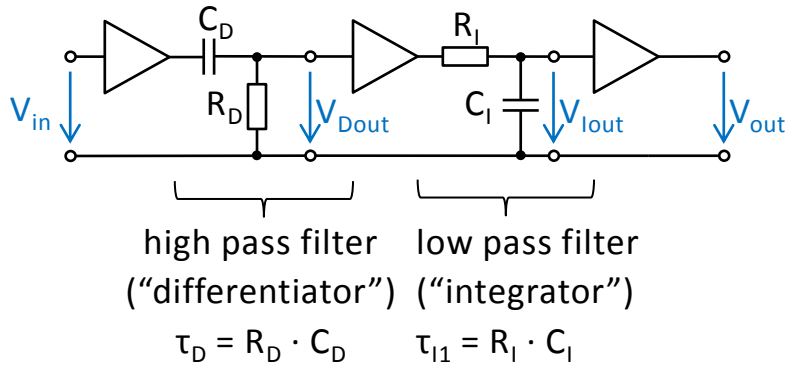
$$= \tau_D \cdot e^{-\frac{t}{\tau_D}} \cdot \lim_{\Delta\tau \rightarrow 0} \left(\frac{\frac{d}{d\Delta\tau} (1 - e^{-t(\frac{\Delta\tau}{\tau_I \tau_D})})}{\frac{d}{d\Delta\tau} (\Delta\tau)} \right)$$

l'Hospital's rule

$$= \tau_D \cdot e^{-\frac{t}{\tau_D}} \cdot \lim_{\Delta\tau \rightarrow 0} \left(\frac{t}{\tau_I \tau_D} \cdot e^{-t(\frac{\Delta\tau}{\tau_I \tau_D})} \right) = \frac{t}{\tau_I} \cdot e^{-\frac{t}{\tau_D}} = \frac{t}{\tau} \cdot e^{-\frac{t}{\tau}}$$

limes, then $\tau_I = \tau_D = \tau$

CR-RC Pulse Shaping (combination of a “differentiator” and an “integrator”):

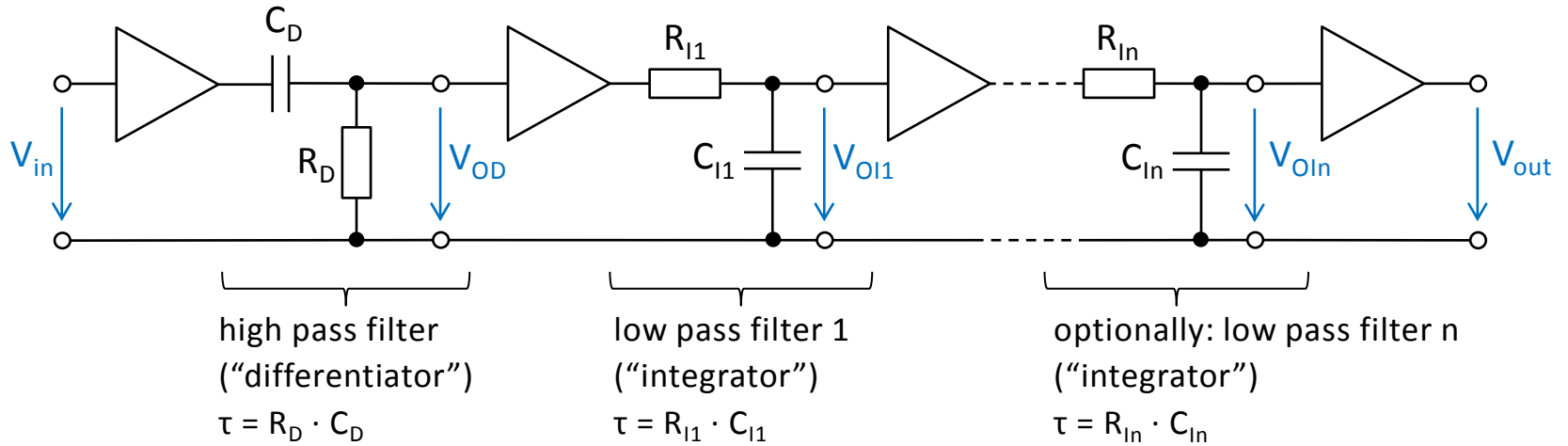


$$G_{DI}(s) = \frac{V_{out}(s)}{V_{in}(s)} = G_D(s) \cdot G_I(s) = \frac{sC_D R_D}{(1 + sC_D R_D) \cdot (1 + sC_I R_I)}$$

Effect of a simple CR-RC Pulse shaping:

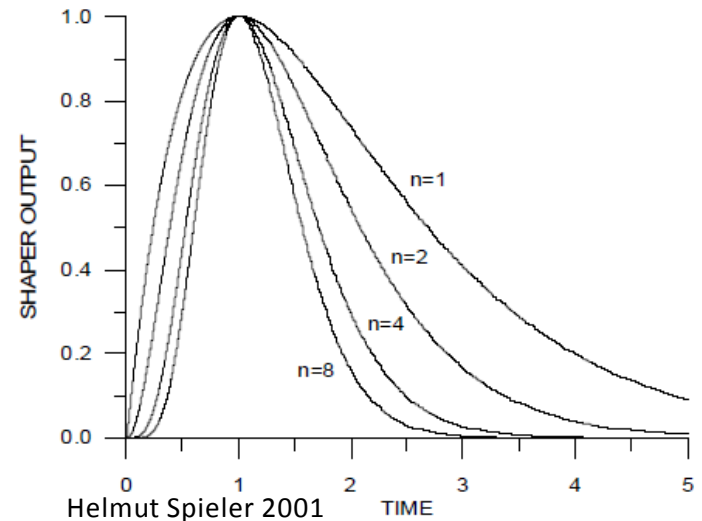
Signal reduced (bad), but much higher reduction of noise => enhancement of S/N-Ratio

1. CR-(RC)ⁿ Pulse Shaping:



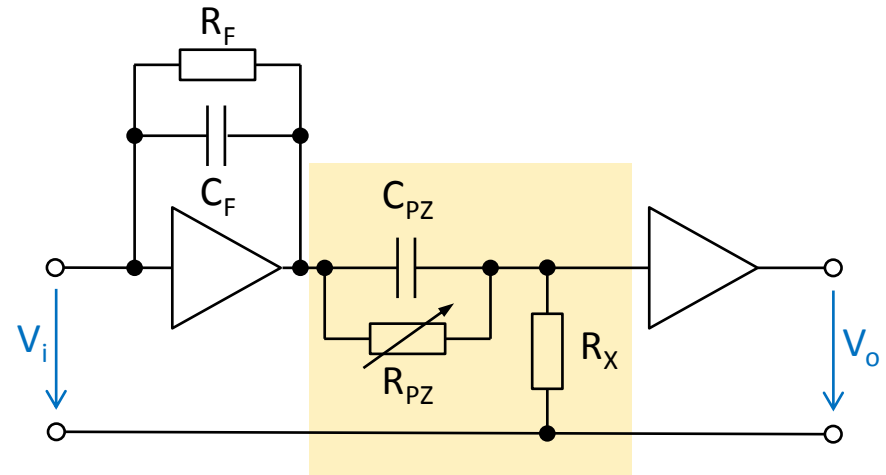
Increasing number of integrators make the output Pulse more symmetrical with a faster return to base-line.

To preserve the peaking time the time constant of the original integrator (for n=1) has to be divided by the number n: $\tau_n = \tau_1 / n$



2. Pole-Zero Cancellation:

- Controls the lower cutoff frequency
- No impact on the upper cutoff freq.
- Can be used for pulse shape and baseline recovery adjustments
- It is not the most efficient but an easy to integrate shaper



Application:

Charge sensitive amplifiers and stabilized transimpedance amplifiers (with a capacitance in their feedback) have a pole at $s=1/C_F R_F$ in their transfer function.

This pole can be compensated with the above circuit (yellow part) which creates a zero.

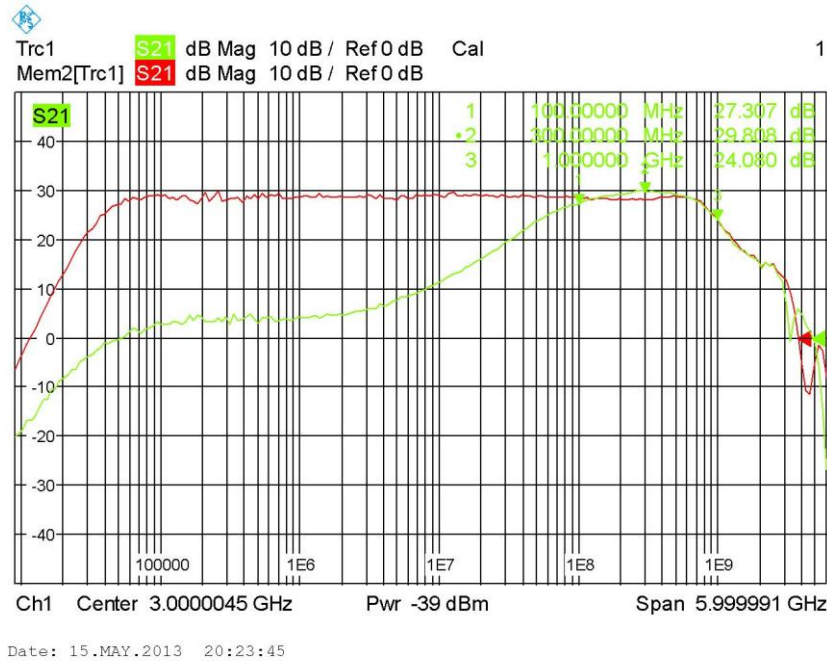
To compensate the pole one has to choose: $C_{PZ} \cdot R_{PZ} = C_F \cdot R_F$

The value of the Resistor R_X has no effect on the zero except it would be zero or infinite.

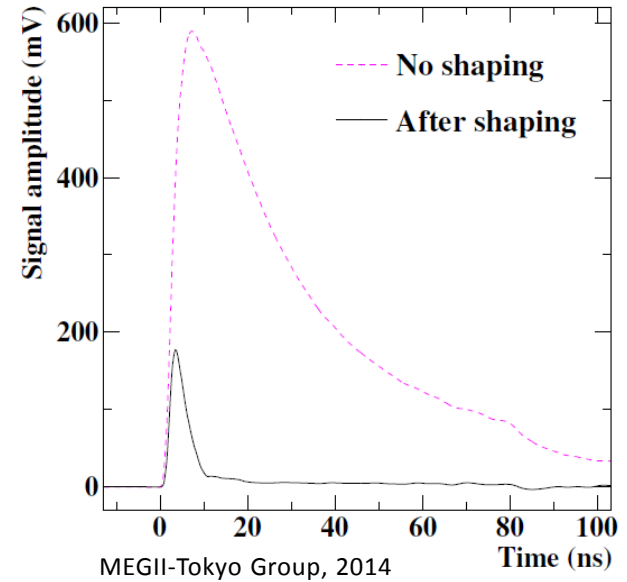
=> pole zero cancellation can be applied as well in other networks for pulse shape and baseline optimization (e.g. for AC-coupled signal paths)

2. Pole-Zero Cancellation:

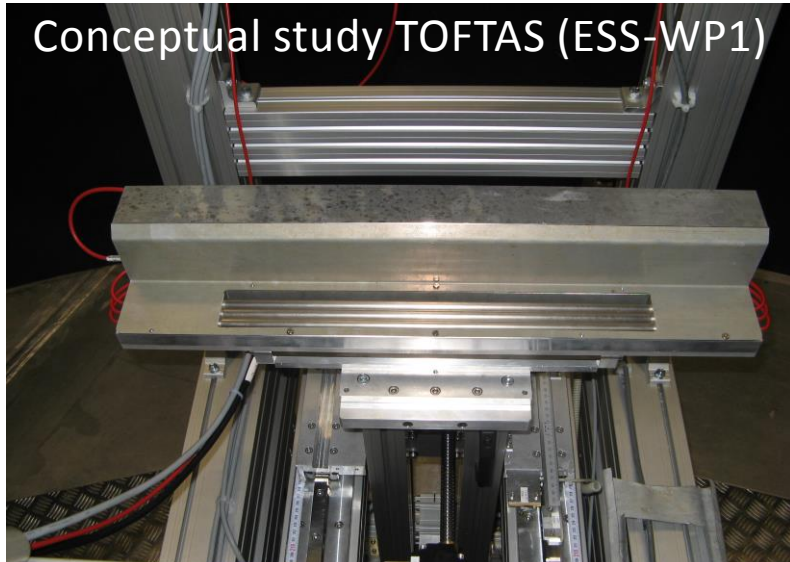
In frequency domain:



in time domain:

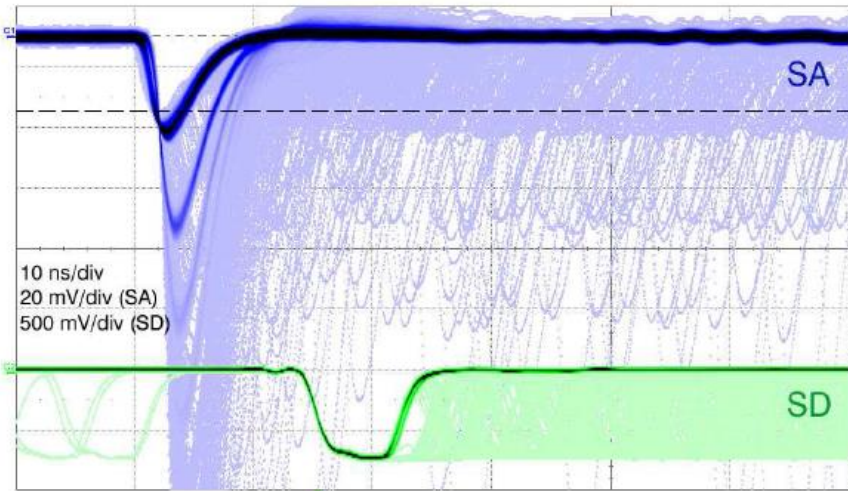
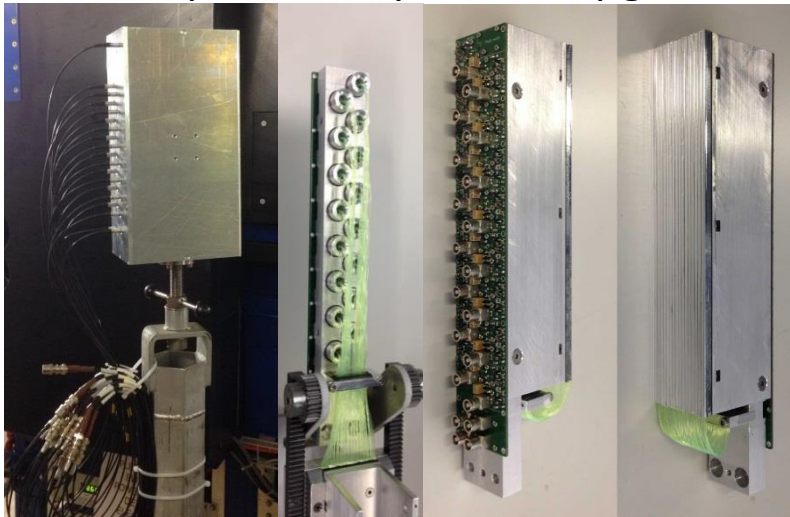
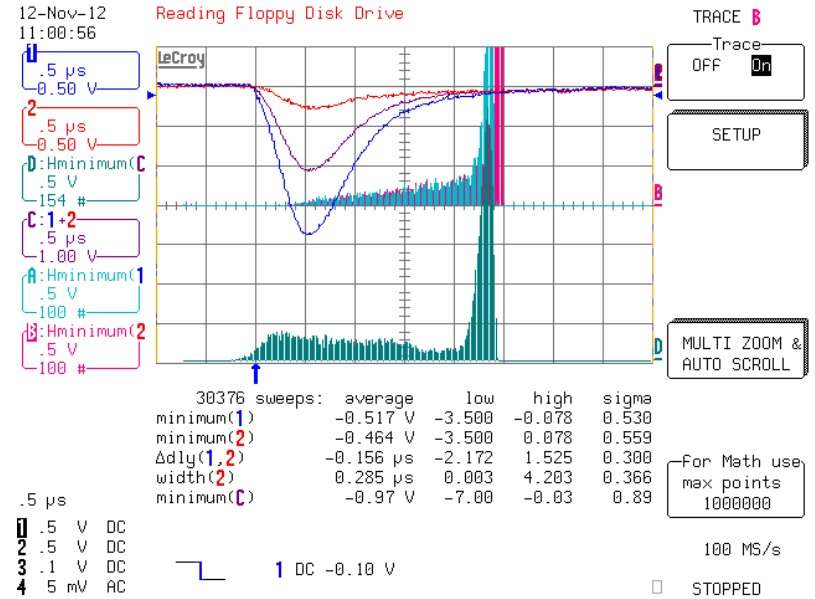


Some Examples



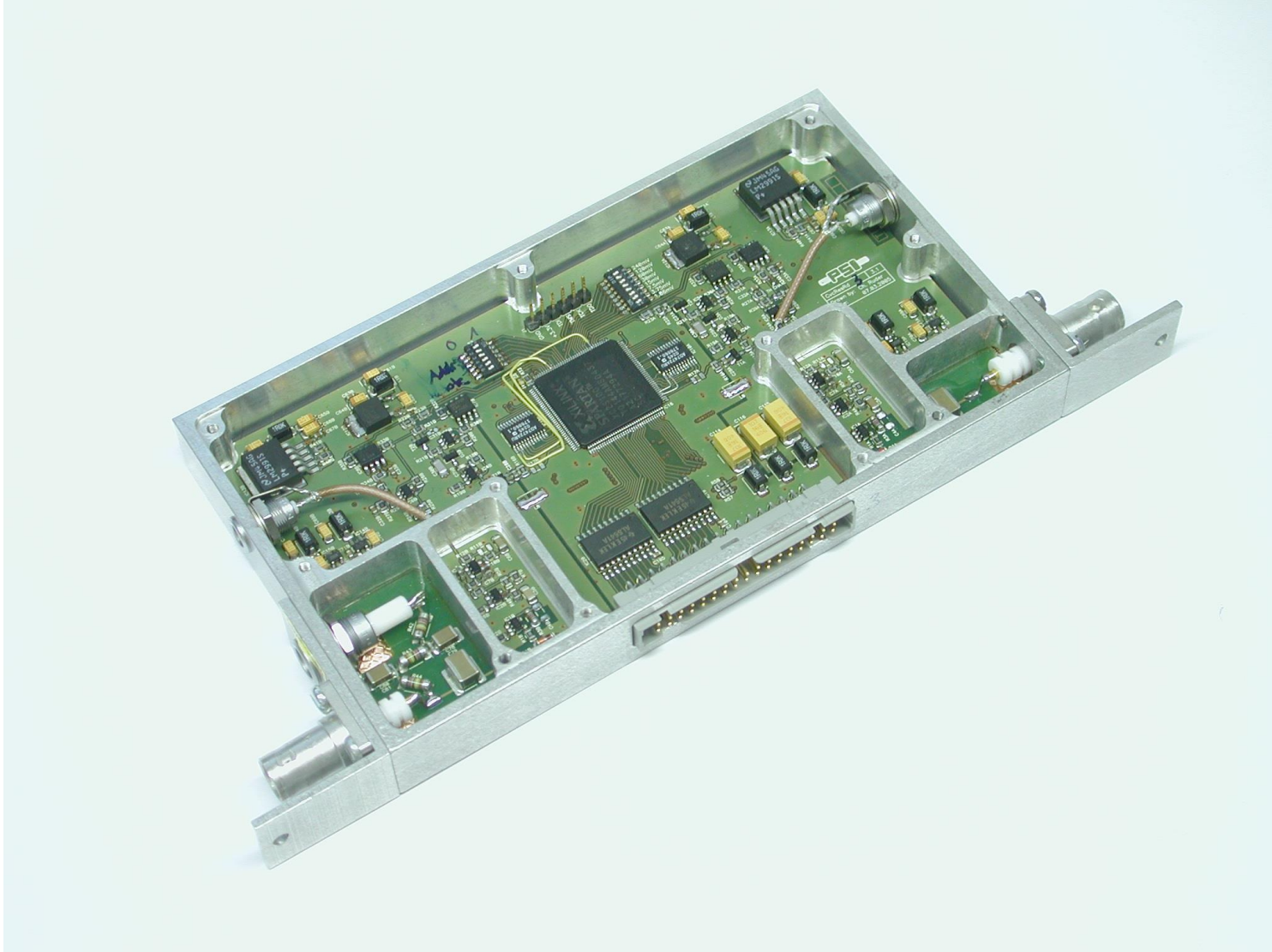
Conceptual study TOFTAS (ESS-WP1)

Conceptual study POLDI-Upgrade

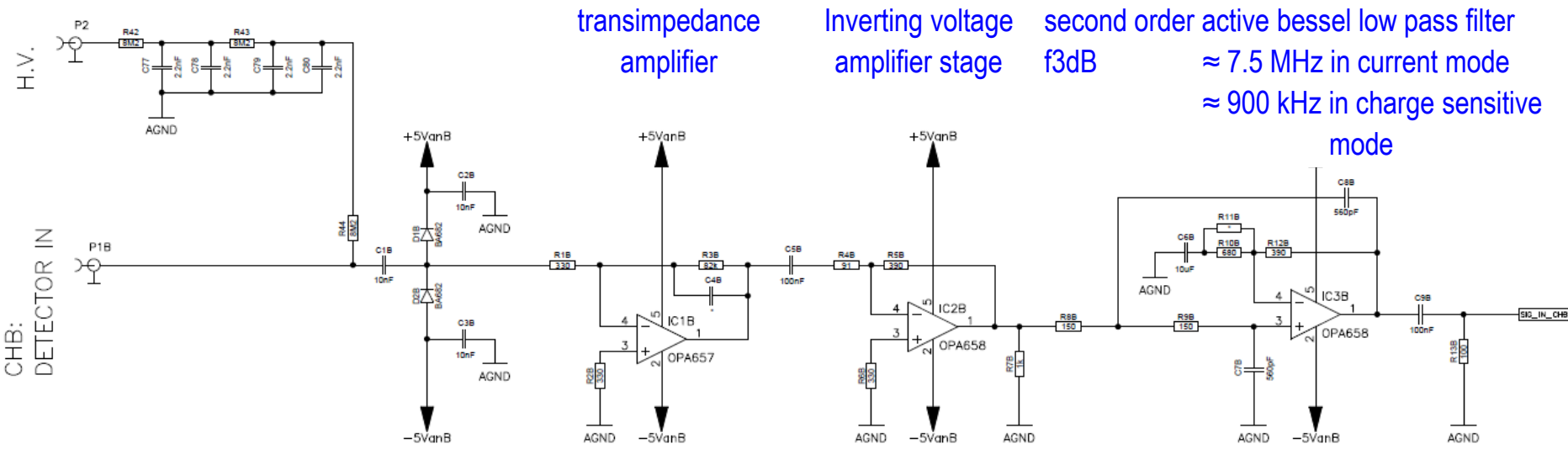


Pictures below: Hildebrand, Stoykov, Mosset

Example: Charge Division Readout



Schematics of the Input Amplifier:

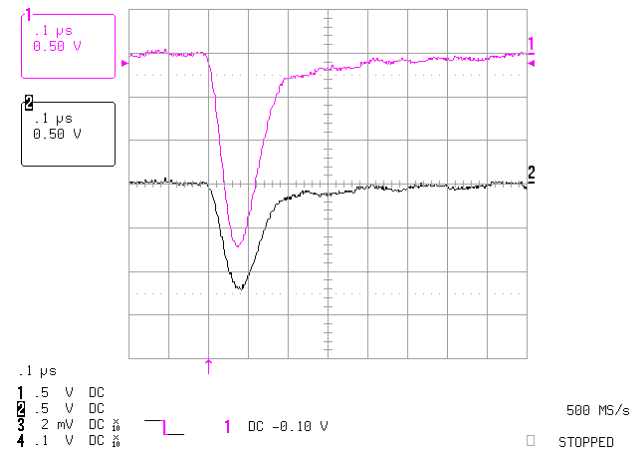


OPA657: FET-input

- GBP = 1.6 GHz
- $T_{\text{rise\&fall}}$ = 1 ns (0.2 V Step)
- T_{settling} = 20 ns (2 V Step)
- Z_{inDiff} = 10 TΩ || 0.7 pF
- Z_{inCM} = 10 TΩ || 4.5 pF
- A_{OL} = 70 dB
- $V_{\text{in-noise}}$ = 4.8 nV/√Hz
- $I_{\text{in-noise}}$ = 1.3 fA/√Hz

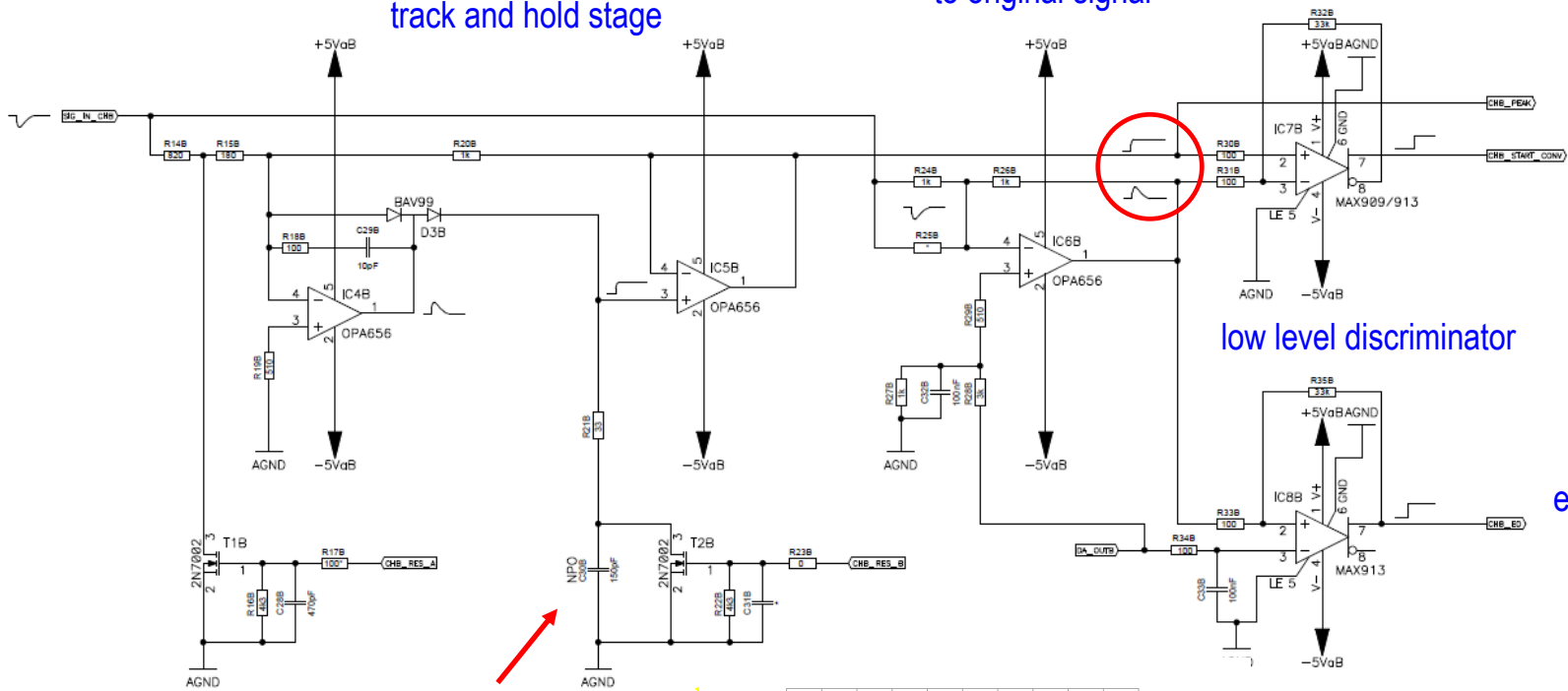
OPA658: Current Feedback

- BW = 900 MHz (unity gain stable)
- SR = 1700V/us
- G/ϕ_{error} = 0.025%/0.02°
- G_{flatness} = 0.1 dB to 135MHz
- I_{out} = 80 mA
- $V_{\text{in-noise}}$ = 45.3 μVrms (to 200 MHz)
- $I_{\text{in-noise}}$ = 32 pA/√Hz



Charge Division Readout – Track and Hold Stage

Schematics of the Track and Hold Stage:



track and hold stage

inverting amplifier
adding an offset
to original signal

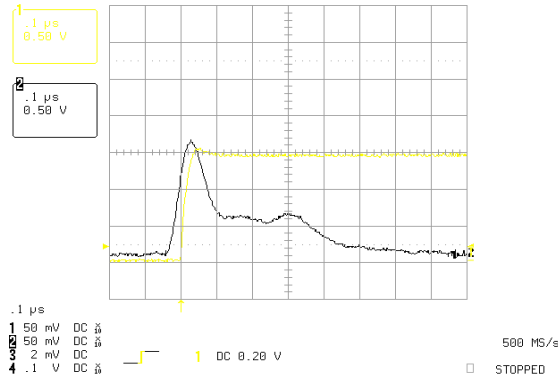
peak-detector

peak signal
to ADC
peak detected
to FPGA

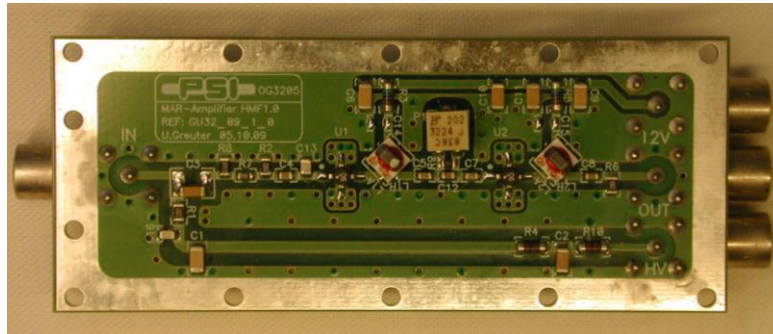
low level discriminator

event detected
to FPGA

analog storage
Happens here



MAR-Amplifier for Photon-Detectors



Functional description:

The “MAR”-Amplifier was designed for fast photo-diode (e.g. APD) applications where due to limited space at the detector-side the photo-diodes has to be off-board and where coax cables are needed to connect them to the amplifiers.

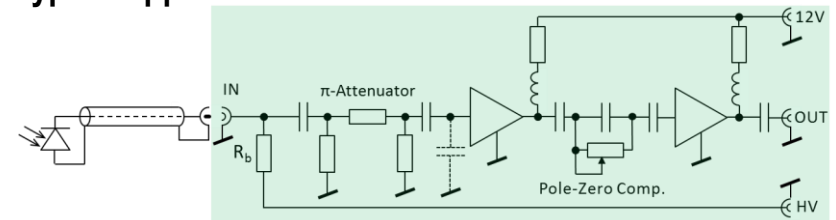
The board layout allows for the assembly of two RF gain blocks which can be chosen from a wide palette of monolithic amplifiers in .085 micro-x or SOT-89 case styles.

Within 50 Ω systems the amplifier can be used either as transimpedance or voltage amplifier. It is cascadable.

The two gain stage amplifier design includes:

- π -attenuator for gain setting
- adjustable pole-zero cancellation for pulse shaping
- integrating capacitor for upper bandwidth limitation
- lower bandwidth adjustment by of AC-coupling capacitor
- filtered high voltage path for reverse bias voltage

Typical application scheme:



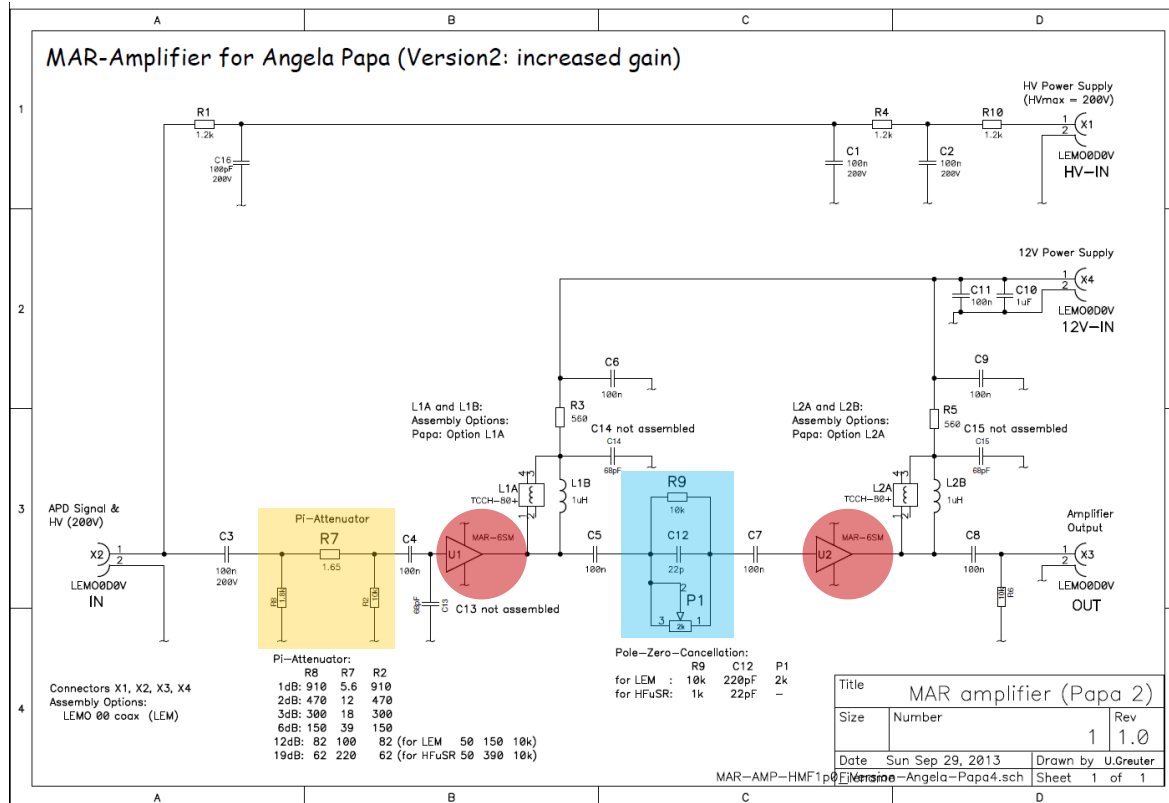
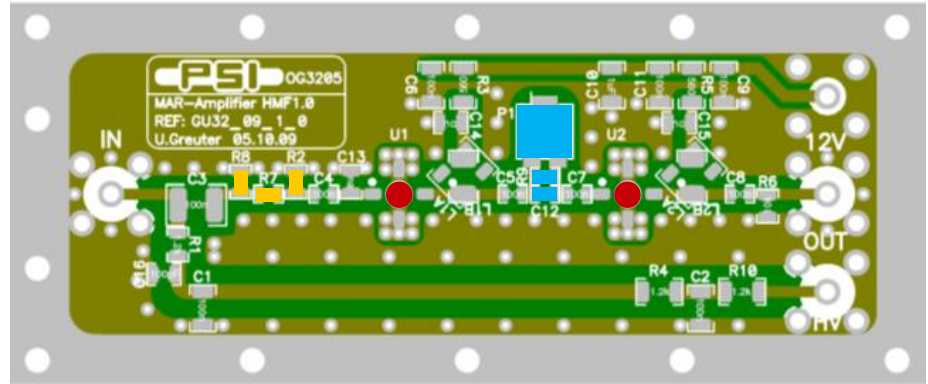
Specifications (with MAR-6SM on both stages):

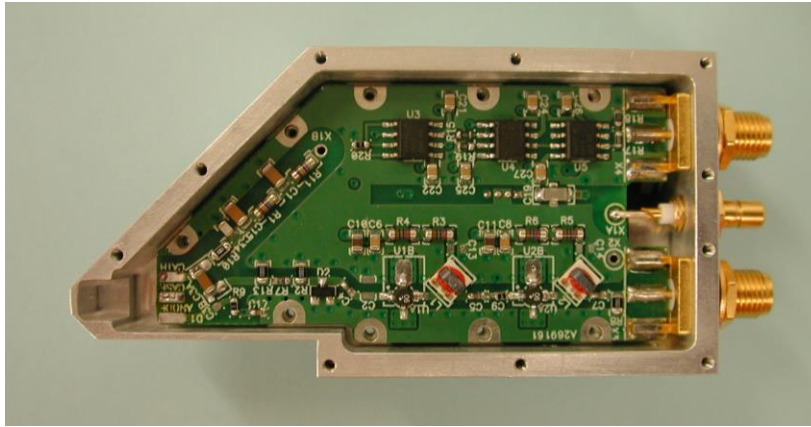
- Input impedance 50 Ω
- primary transimpedance gain 50 V/A
- voltage gain (with no π -attenuation):

Frequency	100 kHz	750 MHz	1 GHz	2 GHz
Gain	40 dB	37 dB	32 dB	22 dB

- linear output range (1dB compression) 342 mV_{rms} @ 50 Ω
- max. reverse bias voltage 200 V
- power-consumption amplifier +12 V, 32 mA

The MAR-Amplifier





Brief description:

Amplifier for fast avalanche photo diodes (e.g. Silicon Sensor, AD230-8, 180 ps rise time) with integrated low and high voltage filters, a current monitor output for the APD bias current and pulse-shaping options like a π -attenuator, an integrating capacitor and a pole-zero cancellation stage.

The board layout allows to read out the APD-signal either on the cathode or anode side. The two RF amplifier stages can be assembled with a wide palette of monolithic amplifiers in .085 micro-x or SOT-89 case styles.

Specifications (MAR-6SM on both stages):

RF-Amplifier Output:

- current to voltage conversion 50 V/A
- voltage gain at frequency

Frequency	100 kHz	750 MHz	1 GHz	2 GHz
Gain	40 dB	37 dB	32 dB	22 dB

- max. output voltage (1dB Comp): 282 mV @ 50 Ω

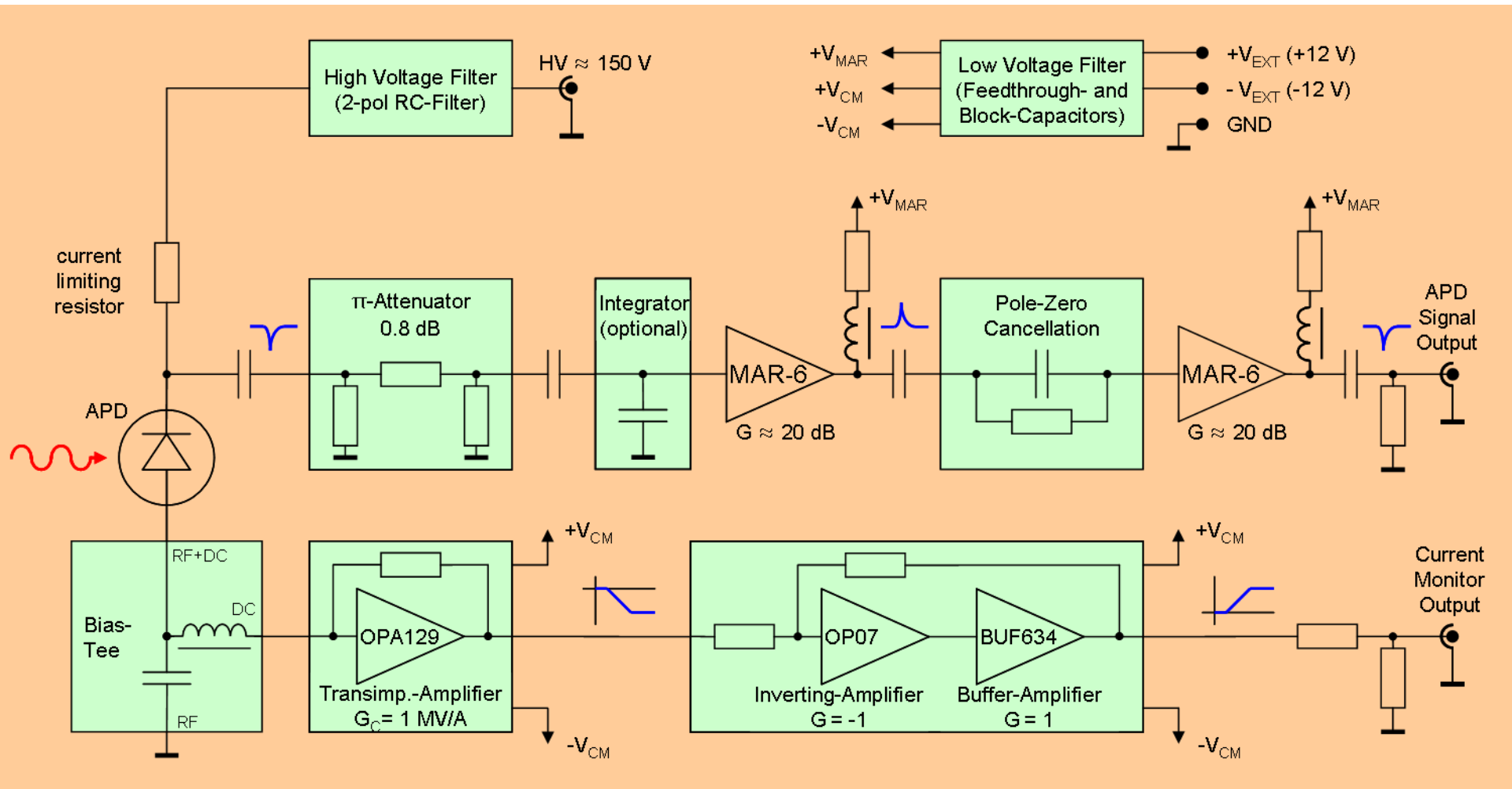
Current Monitor Output:

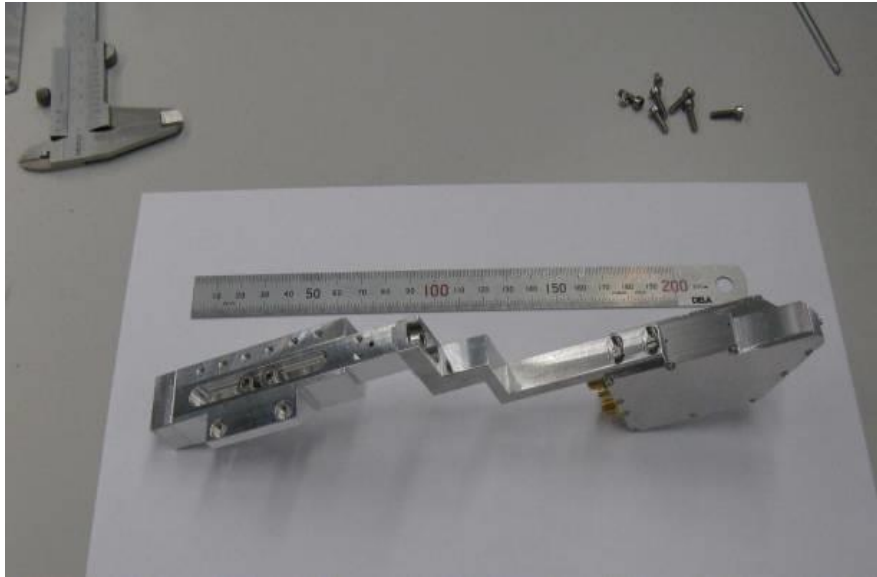
- input current range 0 ... 500 nA
- accuracy < 0.1% full scale
- current to voltage conversion 1 V/ μ A
- bandwidth 1 kHz

Power-Supply:

- Amplifier +/-12V, 300mA
- max. APD - voltage 200 V

MAR-Amplifier for STXM @ PolLux-Beamline





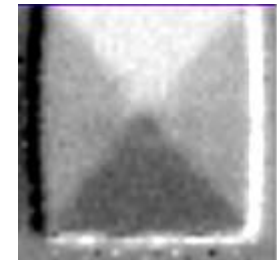
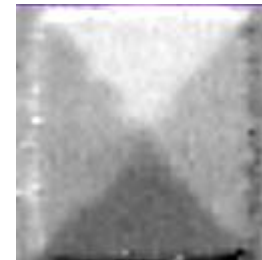
APD-Detector : Urs Greuter, Blagoj Sarafimov, Jörg Raabe, Aleksandar Puzic

Sample: Co (50 nm) / Rh (0.75) / NiFe (50 nm)
FM coupling due to Ne ion irradiation

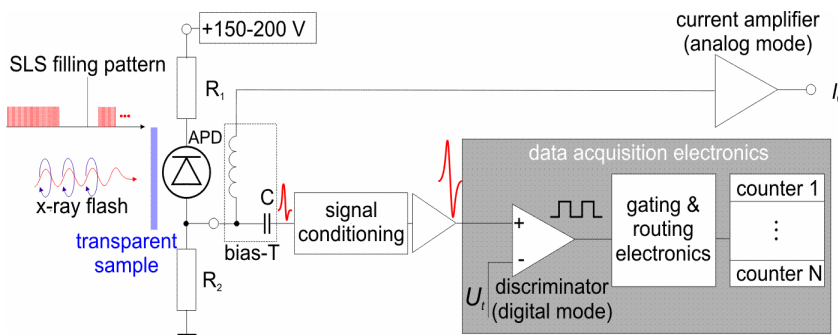


Ni 859.2 eV

Co 783.7 eV



static magnetic imaging:
square 2000 nm x 2000 nm, P+/P-



Principle of detection and data acquisition

Slide received on 24.06.2010
from Jörg Raabe

movie: square 1000 nm x 1000 nm
image size: 1000 nm x 1000 nm
resolution: 15 nm
dwell time: 20ms
2 phases (0 deg & 45 deg) with 4 channels
measured magnetization component:
out-of-plane (vortex core)
Ni (859.2 eV), P-
Excitation:
 $f = 625$ MHz, $B_0 = 2.25$ mT (in plane) field

